





DMG8601UFG

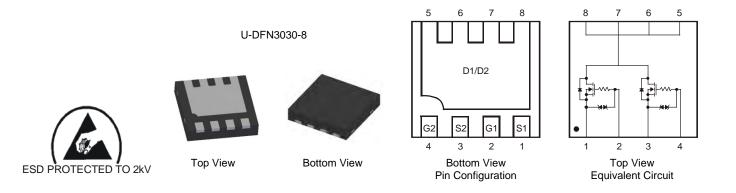
DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208 [♠]
- Polarity: See Diagram
- Weight: 0.0172 grams (approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMG8601UFG-7	U-DFN3030-8	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



2N4 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 09 for 2009) WW = Week code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage		Vgss	±12	V	
Continuous Drain Current (Note 5)	Steady State	TA = +25°C TA = +70°C	lo	6.1 5.2	А
Pulsed Drain Current			IDM	27	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Pb	0.92	W
Thermal Resistance, Junction to Ambient @TA = +25°C	RөJA	136	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

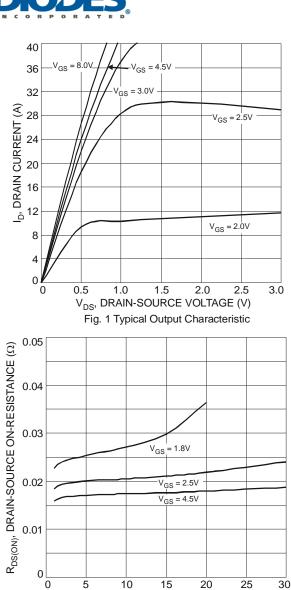
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

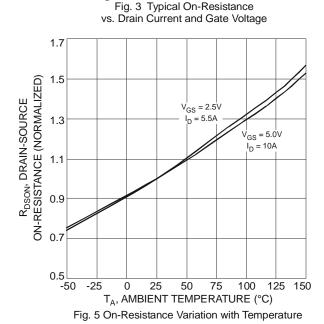
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μА	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	-	V	$V_{DS} = 0V, I_G = \pm 250 \mu A$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.35	-	1.05	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	17	23		$V_{GS} = 4.5V, I_D = 6.5A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	20	27	$m\Omega$	$V_{GS} = 2.5V, I_D = 5.5A$	
	, ,	-	25	34		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 10V, I_{D} = 5A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	-	143	-	pF		
Output Capacitance	Coss	-	74	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	29	-	pF		
Gate Resistance	R_g	-	202	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qq	-	8.8	-	nC		
Gate-Source Charge	Q _{gs}	-	1.4	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q _{qd}	-	3.0	-	nC	$I_D = 6.5A$	
Turn-On Delay Time	t _{D(on)}	-	53	-	ns		
Turn-On Rise Time	t _r	-	78	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	562	-	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	-	234	-	ns		

Notes:

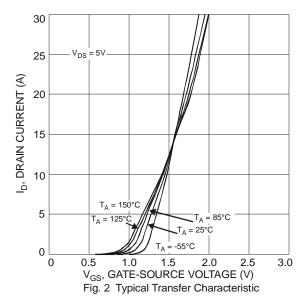
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Short duration pulse test used to minimize self-heating effect.

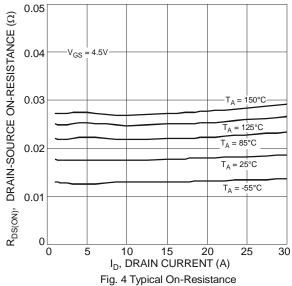






 I_D , DRAIN-SOURCE CURRENT (A)





vs. Drain Current and Temperature 0.05 R_{DSON} DRAIN-SOURCE ON-RESISTANCE (Ω) 0.04 GS = 2.5 0.03 $I_{D} = 5.5A$ V_{GS} = 5.0V I_D = 10A 0.01 0 -50 -25 25 50 75 100 125 150 T_A, AMBIENT TEMPERATURE (°C)

Fig. 6 On-Resistance Variation with Temperature



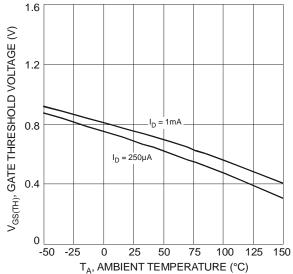


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

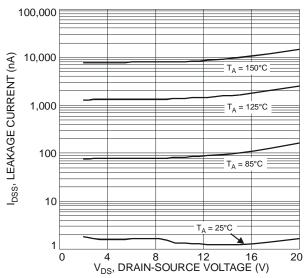


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

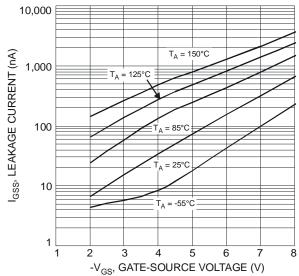
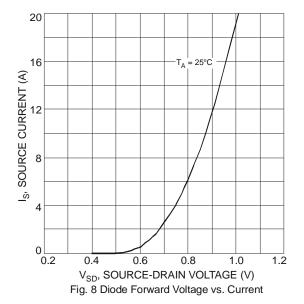
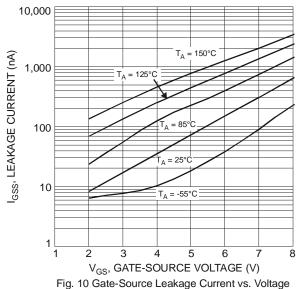


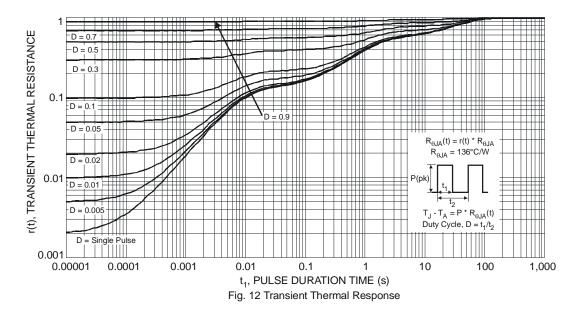
Fig. 11 Gate-Source Leakage Current vs. Voltage





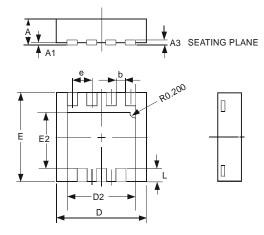
Document number: DS31788 Rev. 5 - 2





Package Outline Dimensions

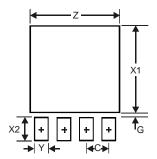
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN3030-8					
Dim	Min	Max	Тур		
Α	0.57	0.63	0.60		
A1	0	0.05	0.02		
А3			0.15		
b	0.29	0.39	0.34		
D	2.90	3.10	3.00		
D2	2.19	2.39	2.29		
е			0.65		
Е	2.90	3.10	3.00		
E2	1.64	1.84	1.74		
L	0.30	0.60	0.45		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Υ	0.39
С	0.65



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2012, Diodes Incorporated

www.diodes.com